

Roll No.

Total No. of Questions : 09]

Total No. of Pages : 02

B.Tech. (Sem. ^U 7th/8th)
OPTICAL FIBER COMMUNICATIONS
SUBJECT CODE : EC - 404
Paper ID : [A0329]

[Note : Please fill subject code and paper ID on OMR]

Time : 03 Hours

Maximum Marks : 60

Instruction to Candidates:

- 1) Section - A is **Compulsory**.
- 2) Attempt any **Four** questions from Section - B.
- 3) Attempt any **Two** questions from Section - C.

Section - A

Q1)

(10 × 2 = 20)

- a) List the various advantages of fiber optical communication system.
- b) Calculate the carrier frequency for an optical communication system operating at 1310 nm.
- c) Distinguish between RZ & NRZ modulation format.
- d) What is the difference between loose & tight buffer fibers in terms of operation?
- e) How light radiation occurs in a p-n junction semiconductor?
- f) What do you understand carrier lifetime of charge carriers in photo detectors.
- g) Explain red and blue shift in optical communication systems.
- h) What is speckle noise?
- i) Why mode partitioning noise is dominant in single mode fibers?
- j) Give your comments upon the statement, "Optical & electrical noises are different".

Section - B

(4 × 5 = 20)

- Q2) Explain the physical meaning of each Maxwell equations.
- Q3) What is the difference between Dispersion and Distortion?
- Q4) Explain the working principle of DFB laser diodes with suitable diagram?
- Q5) A SMF has a normalized frequency 2.40, a core refractive index 1.47 & cladding 1.465 & a core diameter of 9 μm . Find insertion loss if it is having lateral offset of 1 μm .
- Q6) What is Sub Carrier Multiplexing? Explain with suitable example.

Section - C

(2 × 10 = 20)

- Q7) Draw the block diagram of optical communication system and describe the function of each block.
- Q8) Why the junction capacitance & resistance of a photodiode varies with the junction voltage & load resistance. Also list the advantages of using reverse bias in a photodiodes.
- Q9) Suppose an avalanche photodiode has the following parameters: $I_L = 1 \text{ nA}$, $I_D = 1 \text{ nA}$, $n = 0.85$, $F = M^{1/2}$, $R_L = 10^3 \Omega$ & $B = 1 \text{ kHz}$. Consider a sinusoidally varying 850 nm signal, which has modulation index $m = 0.85$ & an average power level $P_0 = -50 \text{ dBm}$, to fall on the detector at room temperature. Plot the S/N ratio as a function of M for gains varying from 20 to 100. At what value of M does the maximum S/N occurs?
